

IN THE CLAIMS

Each claim of the present application is set forth below with a parenthetical notation immediately following the claim number indicating the current claim status. The Examiner's entry of the claim amendments, as shown in marked-up form below, under Section 116 is respectfully requested.

1. (CURRENTLY AMENDED) A physical vapor deposition chamber for depositing material on a wafer, comprising:

a chuck comprising ~~an~~ a planar upper surface and sidewalls extending downwardly therefrom;

a removable pedestal cover having a planar upper surface in contact with ~~overlying~~ the planar upper surface of the chuck and extending laterally beyond the sidewalls, the pedestal cover defining a peripheral circumferential groove therein ~~and comprising a planar upper surface in a region overlying the chuck~~ and a concave lower surface for receiving the chuck therein, wherein a circumference of the wafer extends radially inwardly of an inner sidewall of the groove; and

wherein a planar backside of the wafer is positionable in contact with the planar upper surface of the pedestal cover during material deposition.

2. (ORIGINAL) The physical vapor deposition chamber of claim 1 wherein the pedestal cover further comprises a plurality of pads on an upper surface thereof, such that the wafer may be disposed on the plurality of pads.

3. (ORIGINAL) The physical vapor deposition chamber of claim 1 further comprising an aluminum target for depositing aluminum on the wafer.

4. (CURRENTLY AMENDED) A physical vapor deposition chamber for depositing material on a wafer, comprising:

a chuck comprising ~~an~~ a planar upper surface;

a removable pedestal cover having a planar upper surface in contact with the planar upper surface of the chuck ~~supported by the upper surface~~ and having downwardly directed sidewalls defining an opening; and

wherein the chuck is disposed within the opening and the wafer is positionable over the pedestal cover extending beyond the sidewalls during material deposition.

5. (ORIGINAL) The physical vapor deposition chamber of claim 4 wherein the pedestal cover further comprises a plurality of pads on an upper surface of the pedestal cover, such that the wafer may be disposed on the plurality of pads.

6. (CURRENTLY AMENDED) A pedestal cover for a material deposition process, wherein during the process material is deposited on a semiconductor wafer supported by a chuck, and wherein the pedestal cover is disposed intermediate the chuck and the wafer, the cover comprising:

a removable disk defining a peripheral circumferential trench therein and downwardly directed sidewalls extending from a bottom surface thereof, the sidewalls further defining an opening; and

wherein the wafer is positioned in contact with the disk and the disk is supported by the chuck during the material deposition process, wherein a circumference of the wafer extends radially inwardly of an inner sidewall of the trench.

7. (ORIGINAL) The pedestal cover of claim 6 further comprising a plurality of pads on an upper surface of the disk, such that the wafer may be disposed on the plurality of pads during the material deposition process.

8. (ORIGINAL) The pedestal cover of claim 6 wherein a material of the pedestal cover comprises stainless steel.

9. (ORIGINAL) The pedestal cover of claim 6 wherein the material of the material deposition process is deposited on the pedestal cover during the material deposition process and is removable therefrom.

10. (CURRENTLY AMENDED) A pedestal cover for a material deposition process, wherein during the process material is deposited on a semiconductor wafer supported by a chuck, and wherein the pedestal cover is disposed intermediate the chuck and the wafer, the cover comprising:

a removable disk comprising a support member and sidewalls extending downwardly from a bottom surface of the support member, wherein the sidewalls define an opening;

such that during the material deposition process the chuck may be removably disposed within the opening; and

such that the wafer may be disposed in contact with the support member and extending beyond the sidewalls during the material deposition process.

11. (ORIGINAL) The pedestal cover of claim 10 further comprising a plurality of pads on an support member, such that the wafer is positionable on the plurality of pads during the material deposition process.

12. (ORIGINAL) The pedestal cover of claim 10 wherein a material of the pedestal cover comprises stainless steel.

13. (ORIGINAL) The pedestal cover of claim 10 wherein the material of the material deposition process is deposited on the pedestal cover during the material deposition process and is removable therefrom.

14. (WITHDRAWN) A process for depositing material on a wafer;

providing a chuck;

disposing a pedestal cover over an upper surface of the chuck, the cover defining a peripheral circumferential trench therein;

disposing a wafer in contact with an upper surface of the cover, the trench spaced radially outwardly from a circumference of the wafer; and

depositing material on the wafer during which material is deposited in the trench.